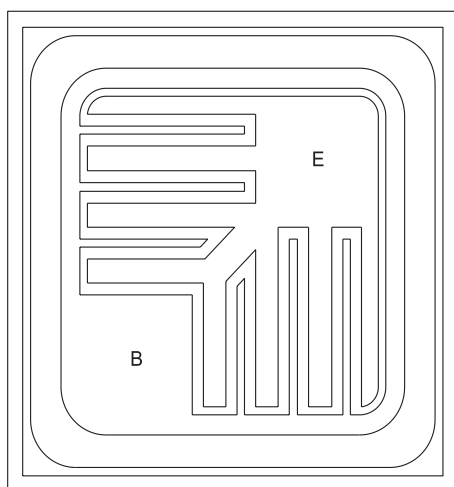


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	30 x 30 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	8.0 x 8.0 MILS
Emitter Bonding Pad Area	7.6 x 7.6 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR

R1

GROSS DIE PER 4 INCH WAFER

12,550

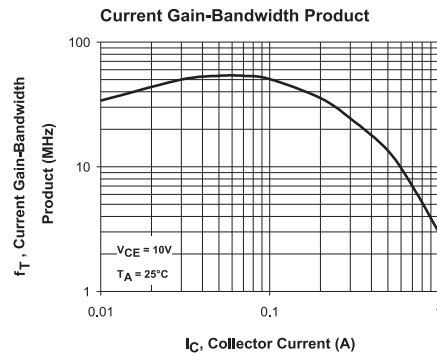
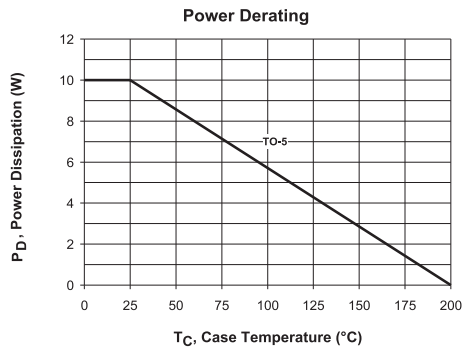
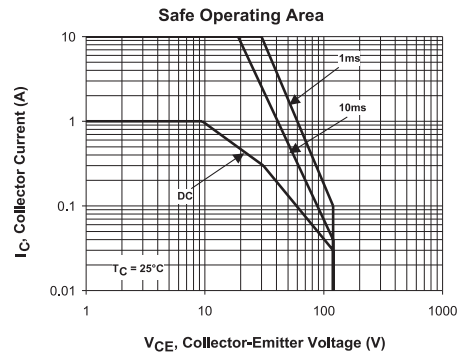
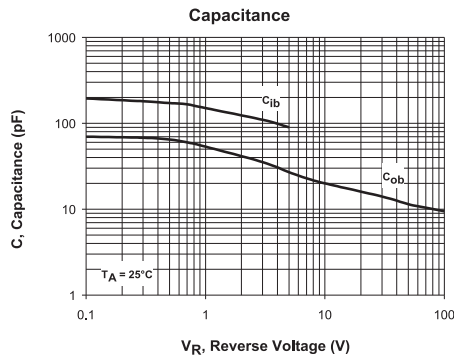
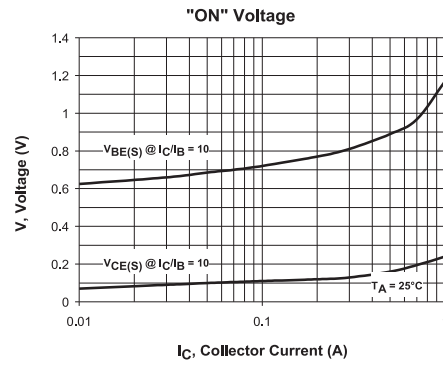
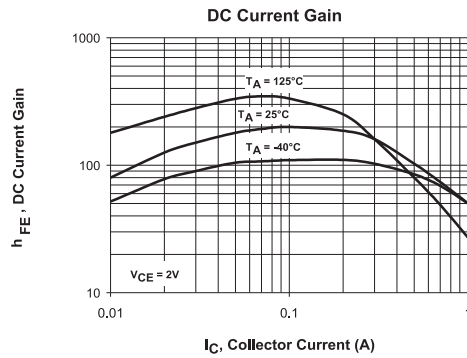
PRINCIPAL DEVICE TYPES

2N5682

2N3501

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